

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	IS&R	L1	2	("20050082573").PN.	US-PGPUB; USPAT; EPO; DERWE NT	2005/12/13 14:35
2	IS&R	L9	1014	(257/345,402,403).CCLS.	US-PGPUB; USPAT; JPO; DERWE NT	2005/12/13 15:00
3	BRS	L10	6	9 and channel near5 (enhancement near3 (implant doping implantation))	US-PGPUB; USPAT; EPO; DERWE NT	2005/12/13 15:05
4	BRS	L12	64463	metal adj oxide adj semiconductor	US-PGPUB; USPAT; JPO; DERWE NT	2005/12/13 15:43
5	BRS	L13	42	12 and channel near5 (enhancement near3 (implant doping implantation))	US-PGPUB; USPAT; EPO; DERWE NT	2005/12/13 15:59
6	BRS	L14	163	12 and gate near5 ((aperture opening via) near3 (implant doping implantation))	US-PGPUB; USPAT; EPO; DERWE NT	2005/12/13 16:00

	Type	L #	Hits	Search Text	DBs	Time Stamp
7	BRS	L16	150	14 and @ad<"20031020"	US- PGPUB; USPAT; EPO; DERWE NT	2005/12/13 16:01

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	33262	('power transistor' dmos dmosfet igbt)	US-PGPUB; USPAT; EPO; DERWE NT	2005/12/13 19:59
2	BRS	L2	2004	1 and gate near3 (opening openings aperture apertures via)	US-PGPUB; USPAT; EPO; DERWE NT	2005/12/13 20:02
3	BRS	L3	206	2 and channel near3 (implant implanting implantation doping doped)	US-PGPUB; USPAT; EPO; DERWE NT	2005/12/13 20:03
4	BRS	L4	187	3 and @ad<"20031020"	US-PGPUB; USPAT; EPO; DERWE NT	2005/12/13 20:03